Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	236	fuse same semiconductor same locat$4 same memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/20 14:57
S2	82	fuse same semiconductor same locat$4 same memory same defect$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 12:28
S3	960	fuse with defect$4 same semiconductor same memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 12:29
S4	53	fuse with defect$4 same semiconductor same memory same locat$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 12:30
S5	6	fuse with defect$4 same semiconductor same memory same locat$4 and (fuse.ti.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 12:37
S6	11	("5835431"|"5933376"|"6008523"|"6119251"|"6266792"|"6408401"|"6477095"|"6479310"|"6578157"|"20020085439"|"20020133770").PN.	US-PGPUB; USPAT	OR	ON	2005/01/12 12:37
S7	11	("5835431"|"5933376"|"6008523"|"6119251"|"6266792"|"6408401"|"6477095"|"6479310"|"6578157"|"20020085439"|"20020133770").PN. and fuse and memory	US-PGPUB; USPAT	OR	ON	2005/01/12 12:37
S8	7	("5835431"|"5933376"|"6008523"|"6119251"|"6266792"|"6408401"|"6477095"|"6479310"|"6578157"|"20020085439"|"20020133770").PN. and fuse with defect$4 and memory	US-PGPUB; USPAT	OR	ON	2005/01/12 12:40
S9	566	test$3 with fuse with defect$5 and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 12:40
S10	57	test$3 with fuse with defect$5 same locat$4 and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 13:41
S11	0	test$3 near fuse near defect$5 same locat$4 and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 12:42

S12	0	test$3 near fuse near defect$5 and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 13:41
S13	73	test$3 with fuse with defect$5 same plurality and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 13:59
S14	0	(test$3 with fuse with defect$5).ti.	US-PGPUB; USPAT	OR	ON	2005/01/12 13:50
S15	11	(test$3 and fuse and defect$5).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 13:51
S16	98	test$3 with fuse same defect$5 same plurality and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 13:57
S17	1	test$3 near fuse same defect$5 same plurality and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 13:57
S18	62	test$3 with defect$4 near fuse and semiconductor and memory	US-PGPUB; USPAT	OR	ON	2005/01/12 14:11
S19	66	test$3 with defect$4 near fuse and memory	US-PGPUB; USPAT	OR	ON	2005/01/12 14:06
S20	2	test$3 with defect$4 near fuse and semiconductor and memory	USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 14:16
S21	54	test$3 near fuse with defect$4 and semiconductor and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 14:18
S22	82	(defect defective) near fuse same test$3 and semiconductor and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 15:09
S23	64	(defect defective) near fuse with test$3 and semiconductor and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 15:09
S24	2	(defect defective) near fuse near test$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 15:12
S25	30	(defect defective) near fuse same test$3 same (semiconductor die wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 15:14

S26	30	(defect defective) near fuse same test$3 same (semiconductor die wafer) and fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 15:19
S27	17	(faulty broken) near fuse same test$3 same (semiconductor die wafer) and fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 17:21
S28	57	fuse near evaluat$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 17:21
S29	17	fuse near evaluat$4 and semiconductor and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 17:21
S30	0	test$3 same common near location same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 11:26
S31	522	test$3 same plurality same location same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 11:27
S32	233	test$3 same plurality same location same semiconductor with device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 11:27
S33	20	test$3 same plurality same location same semiconductor with device same defect$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 11:28
S34	12	test$3 same plurality with semiconductor with device same location same defect$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 16:31
S35	0	ouput near report same (faulty deenerate defective) same fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 12:53

S36	0	ouput near report same (faulty deenerate defective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 12:53
S37	0	ouput near report same (faulty degenerate defective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 12:53
S38	0	test$3 same plurality with semiconductor with device same location same defect$4 and report	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 16:31
S39	3	report with print with defective	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/18 12:18
S40	0	fuse same semiconductor same locat$4 same memory same (defect$4fail$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/15 13:54
S41	106	fuse same semiconductor same locat$4 same memory same (defect$4 fail$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/15 13:54
S42	62	semiconductor same fuse with locat$4 same memory same (defect$4 fail$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/15 13:55
S43	2457	test$4 with fuses!3 same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/15 13:55
S44	371	test$4 with fuses! same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/15 13:56
S45	15	test$4 with fuses! same semiconductor and memory same location same defect$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/15 13:58

S46	3	test$4 near fuses! same semiconductor and memory same location same defect$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/15 13:59
S47	14	test$4 near fuses! same semiconductor and memory same fuse same defect$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/15 13:59
S48	12	test$4 near fuses! same semiconductor and memory same fuse same defect$4 and fuse.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/15 13:59
S49	5	defect$4 with fuse same test$4 and common near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/20 15:17
S50	2	defect$4 near fuse same test$4 and common near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR .	ON	2005/06/20 15:16
S51	0	defect$4 near fuse same test$4 and identical near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/20 15:16
S52	60	defect$4 with fuse same test$4 and sam$2 near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/20 15:22
S53	54	test$4 with fuse and defect$4 with fuse and (sam$2 common) near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/20 15:28
S54	6	test$4 near fuse and defect$4 near fuse and (sam$2 common) near (address location)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/20 16:02
S55	16	output with location with defective with fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/20 16:45

S56	0	output$4 near location with defective near fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/20 16:03
S57	0	output$4 near location with defect$4 near fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/20 16:03
S58	16	output$4 with location with defect$4 with fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 11:29
S59	2	output$4 with location with defect$4 with fuse and common near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 12:03
S60	1	test$4 near fuses same common near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 12:04
S61	1	test$4 near fuses same sam$2 near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 12:05
S62	2	test$4 with fuses same sam$2 near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 12:05
S63	4	test$4 with fuses same (common sam$2) near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 12:06
S64	7	test$4 with fuses same (common sam$2) near address	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 12:06
S65	18	test$4 with (common sam$2) with (location address) and test$4 near fuse and defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:26

S66	12	(common sam$2) with (location address) and test$4 near fuse and defect$4 near fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:40
S67	4	(common sam$2) with (location address) and test$4 near fuse and defect$4 near fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:59
S68	2	defective adj fuse and test$4 near fuses! and (common sam$2) near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:42
S69	2	defect$4 adj fuse and test$4 near fuses! and (common sam$2) near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:42
S70	1	blown adj fuse and test$4 near fuses! and (common sam$2) near location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:43
S71	4	report with defect$4 with fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:44
S72	103	test$4 near fuse same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:45
S73	82	test$4 near fuse same semiconductor and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:45
S74	6	test$4 near fuse same semiconductor and memory and defective near fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:47
S75	0	test$4 near fuse same semiconductor and memory and defective near fuse with frequent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:47

S76	0	test$4 near fuse and semiconductor and memory and defective near fuse with frequent$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:47
S77	2	test$4 near fuse and semiconductor and memory and defective near fuse with locat$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:48
S78	161	fuse with location with defect$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:48
S79	68	fuse with location with defect$4 and memory and test$4 with fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:48
S80	14	fuse with location with defect$4 and memory and test$4 with fuse and fuse.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:49
S81	5	fuse with location with defect$4 and memory and test$4 near fuse and fuse.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:50
S82	0	fuse with location with broken and memory and test$4 near fuse and fuse.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:51
S83	16	output$4 with location with (broken defective) with fuses	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:56
S84	12	test$4 with plurality with fuses! with devices!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:57
S85	2408636	test$4 with plurality with fuses! with devices! and test$3 near$3 fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:58

S86	3	test$4 with plurality with fuses! with devices! and test$3 near fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 13:58
S87	0	corresponding with (location address) and test$4 near fuse and defect$4 near fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:01
S88	2	correspond$4 with (location address) and test$4 near fuse and defect$4 near fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:04
S89	2451	test$4 with fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:04
S90	315	test$4 near fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:05
S91	4	test$4 near plurality near fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:05
S92	12	test$4 near fuses! and (defective broken) near fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:07
S93	4	test$4 near fuses! and (defective broken) near fuses! and (semiconductor wafer die)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:06
S94	38	test$4 near fuses! and (blown) near fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:07
S95	20	test$4 near fuses! and (blown) near fuses! and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:12

S96	0	rate near failure near fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:13
S97	21	rate with fail$4 with fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:13
S98	2	rate with fail$4 with fuses! and test$4 near fuses!	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:16
S99	180	324/550.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:17
S10 0	32	324/550.ccls. and location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:17
S10 1	13	324/550.ccls. and location and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:18
S10 2	7	324/550.ccls. and location and semiconductor and fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/21 14:19